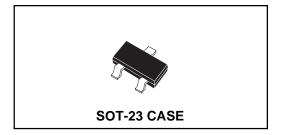
查询CMPT2907A供应商

CMPT2907A

PNP SILICON TRANSISTOR





DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2907A type is an PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

Marking Code is C2F.

MAXIMUM RATINGS (T_A=25°C)

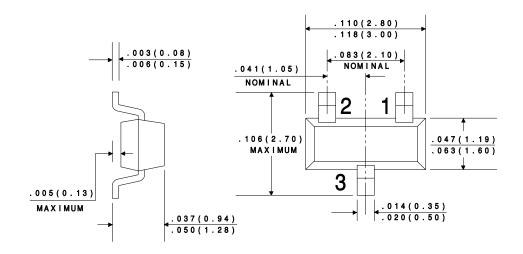
	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	VEBO	5.0	V
Collector Current	I _C	600	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T _J ,T _{stg}	-65 to +150	°C
Thermal Resistance	$\Theta_{\sf JA}$	357	oC/W

ELECTRICAL CHARACTERISTICS $(T_A=25^{\circ}C \text{ unless otherwise noted})$

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICBO	V _{CB} =50V		10	nA
ICBO	$V_{CB} = 50V, T_A = 125^{\circ}C$		10	μΑ
ICEV	$V_{CE}=30V, V_{BE}=0.5V$		50	nA
BVCBO	I _C =10μA	60		V
BVCEO	I _C =10mA	60		V
BVEBO	I _E =10μΑ	5.0		V
VCE(SAT)	I _C =150mA, I _B =15mA		0.4	V
VCE(SAT)	I _C =500mA, I _B =50mA		1.6	V
VBE(SAT)	I _C =150mA, I _B =15mA		1.3	V
VBE(SAT)	I _C =500mA, I _B =50mA		2.6	V
h _{FE}	V _{CF} =10V, I _C =0.1mA	75		
h _{FE}	V _{CE} =10V, I _C =1.0mA	100		
hFE	V _{CE} =10V, I _C =10mA	100		
hFE	V _{CE} =10V, I _C =150mA	100	300	

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
hFE	V _{CE} =10V, I _C =500mA	50		
f _T	V _{CE} =20V, I _C =50mA, f=100MHz	200		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		8.0	pF
C _{ib}	$V_{BE}=2.0V, I_{C}=0, f=1.0MHz$		30	pF
ton	V _{CC} =30V, V _{BE} =0.5, I _C =150mA, I _{B1} =15mA		45	ns
t_d	V _{CC} =30V, V _{BE} =0.5, I _C =150mA, I _{B1} =15mA		10	ns
tr	V _{CC} =30V, V _{BE} =0.5, I _C =150mA, I _{B1} =15mA		40	ns
toff	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		100	ns
t _S	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		80	ns
t _f	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		30	ns

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR